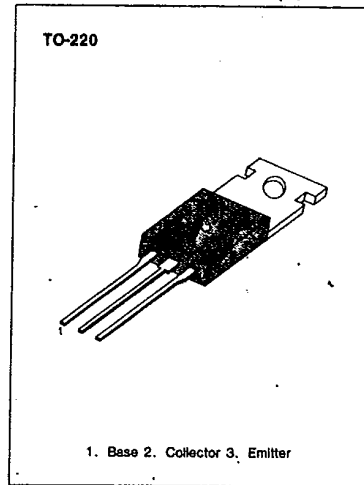


**KSC2233****NPN EPITAXIAL SILICON TRANSISTOR****B/W TV HORIZONTAL DEFLECTION OUTPUT**

- Collector-Base Voltage:  $V_{CB0} = 200V$
- Collector Current (D.C):  $I_C = 4A$
- Collector Dissipation:  $P_C = 40W$

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	200	V
Collector-Emitter Voltage	$V_{CE0}$	60	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Collector Current	$I_C$	4	A
Collector Dissipation ( $T_C = 25^\circ C$ )	$P_C$	40	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~ +150	$^\circ C$



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**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CB0}$	$I_C = 1mA, I_E = 0$	200			V
Collector-Emitter Breakdown Voltage	$BV_{CE0}$	$I_C = 20mA, I_B = 0$	60			V
Emitter-Base Breakdown Voltage	$BV_{EB0}$	$I_E = -1mA, I_C = 0$	5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 170V, I_E = 0$			10	$\mu A$
DC Current Gain	$h_{FE1}$	$V_{CE} = 5V, I_C = 1A$	30		150	
	$h_{FE2}$	$V_{CE} = 5V, I_C = 4A$	20	40		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 0.4A$			1	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 4A, I_B = 0.4A$			1.5	V
Current Gain-Band Width Product	$f_T$	$V_{CE} = 5V, I_C = 0.5A$		10		MHz

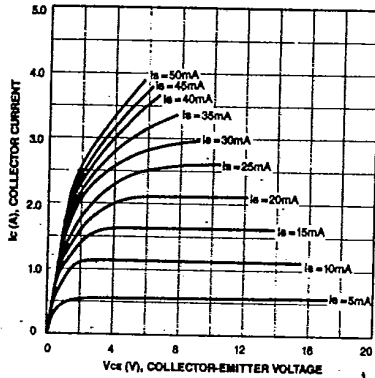


KSC2233

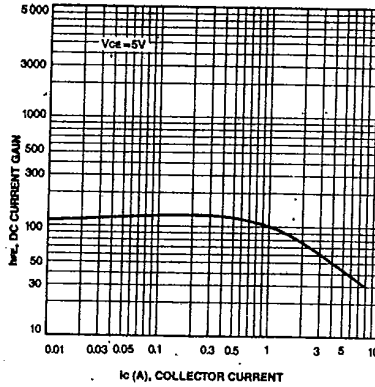
NPN EPITAXIAL SILICON TRANSISTOR

T-33-11

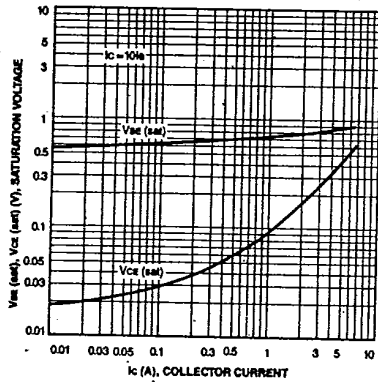
STATIC CHARACTERISTIC



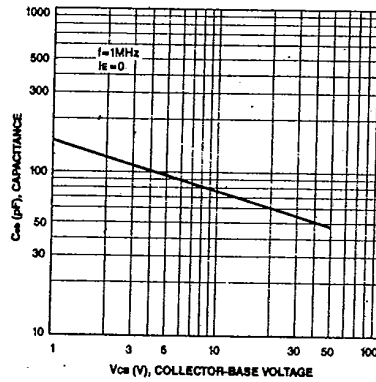
DC CURRENT GAIN



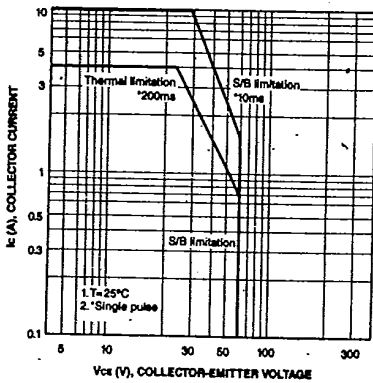
BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



SAFE OPERATING AREA



POWER DERATING

